TS5A3166
0.9-Ω SPST ANALOG SWITCH

SCDS186 − FEBRUARY 2005

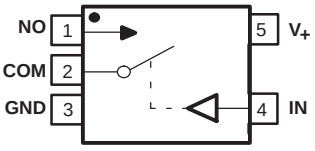
Description

The TS5A3166 is a single-pole single-throw (SPST) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers a low ON-state resistance. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

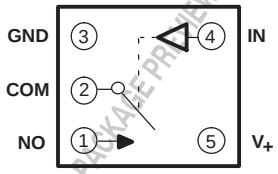
Applications

- **Cell Phones**
- **PDAs**
- **Portable Instrumentation**
- **Audio and Video Signal Routing**
- **Low-Voltage Data-Acquisition Systems**
- **Communication Circuits**
- **Modems**
- **Hard Drives**
- **Computer Peripherals**
- **Wireless Terminals and Peripherals**
- **Microphone Switching – Notebook Docking**

SOT-23 OR SC-70 PACKAGE
(TOP VIEW)



YEP OR YZP PACKAGE
(BOTTOM VIEW)



FUNCTION TABLE

IN	NO TO COM, COM TO NO
L	OFF
H	ON

Features

- **Isolation in the Powered-Off Mode, V_+ = 0**
- **Low ON-State Resistance (0.9 Ω)**
- **Control Inputs Are 5.5-V Tolerant**
- **Low Charge Injection**
- **Low Total Harmonic Distortion (THD)**
- **1.65-V to 5.5-V Single-Supply Operation**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **2000-V Human-Body Model (A114-B, Class II)**
  - **1000-V Charged-Device Model (C101)**

Summary of Characteristics

V_+ = 5 V, T_A = 25°C

Configuration	Single Pole Single Throw (SPST)
Number of channels	1
ON-state resistance (r_{on})	0.9 Ω
ON-state resistance flatness ($r_{on(flat)}$)	0.15 Ω
Turn-on/turn-off time (t_{ON}/t_{OFF})	7.5 ns/12.5 ns
Charge injection (Q_C)	1 pC
Bandwidth (BW)	200 MHz
OFF isolation (O_{ISO})	−64 dB at 1 MHz
Total harmonic distortion (THD)	0.005%
Leakage current ($I_{COM(OFF)}$)	±20 nA
Power-supply current (I_+)	0.5 µA
Package option	5-pin DSBGA, SOT-23, or SC-70

ORDERING INFORMATION

T_A	PACKAGE(1)		ORDERABLE PART NUMBER	TOP-SIDE MARKING(2)
−40°C to 85°C	NanoStar™ − WCSP (DSBGA) 0.23-mm Large Bump − YEP	Tape and reel	TS5A3166YEPR	PACKAGE PREVIEW
	NanoFree™ − WCSP (DSBGA) 0.23-mm Large Bump − YZP (Pb-free)	Tape and reel	TS5A3166YZPR	
	SOT (SOT-23) − DBV	Tape and reel	TS5A3166DBVR	JAS_
	SOT (SC-70) − DCK	Tape and reel	TS5A3166DCKR	JF_

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
(2) DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.
YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, ● = Pb-free).

Absolute Minimum and Maximum Ratings(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_+	Supply voltage range(3)		−0.5	6.5	V
V_{NO} V_{COM}	Analog voltage range(3)(4)(5)		−0.5	V_+ + 0.5	V
I_K	Analog port diode current	V_{NO}, V_{COM} < 0	−50		mA
I_{NO}	On-state switch current	V_{NO}, V_{COM} = 0 to V_+	−200	200	mA
I_{COM}	On-state peak switch current(6)		−400	400	
V_I	Digital input voltage range(3)(4)		−0.5	6.5	V
I_{IK}	Digital input clamp current	V_I < 0	−50		mA
I_+	Continuous current through V_+			100	mA
I_{GND}	Continuous current through GND		−100		mA
θ_{JA}	Package thermal impedance(7)	DBV package		206	°C/W
		DCK package		252	
		YEP/YZP package		132	
T_{stg}	Storage temperature range		−65	150	°C

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(3) All voltages are with respect to ground, unless otherwise specified.
(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(5) This value is limited to 5.5 V maximum.
(6) Pulse at 1-ms duration < 10% duty cycle
(7) The package thermal impedance is calculated in accordance with JESD 51-7.

Electrical Characteristics for 5-V Supply(1)

V_+ = 4.5 V to 5.5 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
Peak ON resistance	r_{peak}	$0 \le V_{NO} \le V_+$, I_{COM} = −100 mA,	Switch ON, See Figure 13	25 °C	4.5 V		0.8	1.1	Ω
				Full				1.2	
ON-state resistance	r_{on}	V_{NO} = 2.5 V, I_{COM} = −100 mA,	Switch ON, See Figure 13	25°C	4.5 V		0.7	0.9	Ω
				Full				1	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = −100 mA	Switch ON, See Figure 13	25°C	4.5 V		0.15		Ω
		V_{NO} = 1 V, 1.5 V, 2.5 V, I_{COM} = −100 mA		25°C			0.09	0.15	
				Full				0.15	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 1 V, V_{COM} = 4.5 V, or V_{NO} = 4.5 V, V_{COM} = 1 V	Switch OFF, See Figure 14	25°C	5.5 V	−20	4	20	nA
				Full		−100		100	
	$I_{NO(PWROFF)}$	V_{NO} = 0 to 5.5 V, V_{COM} = 5.5 V to 0		25°C	0 V	−5	0.4	5	µA
				Full		−15		15	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 1 V, V_{NO} = 4.5 V, or V_{COM} = 4.5 V, V_{NO} = 1 V	Switch OFF, See Figure 14	25°C	5.5 V	−20	4	20	nA
				Full		−100		100	
	$I_{COM(PWROFF)}$	V_{NO} = 0 to 5.5 V, V_{COM} = 5.5 V to 0		25°C	0 V	−5	0.4	5	µA
				Full		−15		15	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 1 V, V_{COM} = Open, or V_{NO} = 4.5 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	5.5 V	−2	0.3	2	nA
				Full		−20		20	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NO} = Open, or V_{COM} = 4.5 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	5.5 V	−2	0.3	2	nA
				Full		−20		20	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		2.4		5.5	V
Input logic low	V_{IL}			Full		0		0.8	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	5.5 V	−2	0.3	2	nA
				Full		−20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 5-V Supply(1) (continued)

V_+ = 4.5 V to 5.5 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	2.5	4.5	7	ns
				Full	4.5 V to 5.5 V	1.5		7.5	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	6	9	11.5	ns
				Full	4.5 V to 5.5 V	4		12.5	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 20	25°C	5 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	5 V		19		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	5 V		18		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	5 V		35.5		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	5 V		35.5		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	5 V		2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	5 V		200		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 19	25°C	5 V		−64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	5 V		0.005		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	5.5 V		0.01	0.1	µA
				Full				0.5	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 3.3-V Supply(1)

V_+ = 3 V to 3.6 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
Peak ON resistance	r_{peak}	$0 \le V_{NO} \le V_+$, I_{COM} = −100 mA,	Switch ON, See Figure 13	25 °C	3 V		1.1	1.5	Ω
				Full				1.7	
ON-state resistance	r_{on}	V_{NO} = 2 V, I_{COM} = −100 mA,	Switch ON, See Figure 13	25°C	3 V		1	1.4	Ω
				Full				1.5	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = −100 mA	Switch ON, See Figure 13	25°C	3 V		0.2		Ω
		V_{NO} = 2 V, 0.8 V, I_{COM} = −100 mA		25°C			0.09	0.15	
				Full				0.15	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 1 V, V_{COM} = 3 V, or V_{NO} = 3 V, V_{COM} = 1 V	Switch OFF, See Figure 14	25°C	3.6 V	−2	0.5	2	nA
				Full		−20		20	
	$I_{NO(PWROFF)}$	V_{NO} = 0 to 3.6 V, V_{COM} = 3.6 V to 0		25°C	0 V	−1	0.1	1	µA
				Full		−5		5	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 1 V, V_{NO} = 3 V, or V_{COM} = 3 V, V_{NO} = 1 V	Switch OFF, See Figure 14	25°C	3.6 V	−2	0.5	2	nA
				Full		−20		20	
	$I_{COM(PWROFF)}$	V_{COM} = 0 to 3.6 V, V_{NO} = 3.6 V to 0		25°C	0 V	−1	0.1	1	µA
				Full		−5		5	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 1 V, V_{COM} = Open, or V_{NO} = 3 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	3.6 V	−2	0.2	2	nA
				Full		−20		20	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NO} = Open, or V_{COM} = 3 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	3.6 V	−2	0.2	2	nA
				Full		−20		20	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		2		5.5	V
Input logic low	V_{IL}			Full		0		0.8	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	3.6 V	−2	0.3	2	nA
				Full		−20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 3.3-V Supply(1) (continued)

V_+ = 3 V to 3.6 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	3.3 V	2	5	10	ns
				Full	3 V to 3.6 V	1.5		11	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	3.3 V	6.5	9	12	ns
				Full	3 V to 3.6 V	4		13	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 20	25°C	3.3 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		19		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		18		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	3.3 V		36		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	3.3 V		36		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	3.3 V		2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	3.3 V		200		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 19	25°C	3.3 V		−64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	3.3 V		0.01		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	3.6 V		0.01	0.1	µA
				Full				0.25	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 2.5-V Supply(1)

V_+ = 2.3 V to 2.7 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
Peak ON resistance	r_{peak}	$0 \le V_{NO} \le V_+$, I_{COM} = −8 mA,	Switch ON, See Figure 13	25 °C	2.3 V		1.4	2.2	Ω
				Full				2.4	
ON-state resistance	r_{on}	V_{NO} = 1.8 V, I_{COM} = −8 mA,	Switch ON, See Figure 13	25°C	2.3 V		1.2	1.8	Ω
				Full				2	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = −8 mA	Switch ON, See Figure 13	25°C	2.3 V		0.5		Ω
		V_{NO} = 0.8 V, 1.8 V, I_{COM} = −8 mA		25°C			0.2	0.5	
				Full				0.5	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 0.5 V, V_{COM} = 2.3 V, or V_{NO} = 2.3 V, V_{COM} = 0.5 V	Switch OFF, See Figure 14	25°C	2.7 V	−2	0.5	2	nA
				Full		−20		20	
	$I_{NO(PWROFF)}$	V_{NO} = 0 to 2.7 V, V_{COM} = 2.7 V to 0		25°C	0 V	−1	0.1	1	µA
				Full		−5		5	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 0.5 V, V_{NO} = 2.3 V, or V_{COM} = 0.5 V, V_{NO} = 2.3 V	Switch OFF, See Figure 14	25°C	2.7 V	−2	0.5	2	nA
				Full		−20		20	
	$I_{COM(PWROFF)}$	V_{COM} = 0 to 2.7 V, V_{NO} = 2.7 V to 0		25°C	0 V	−1	0.1	1	µA
				Full		−5		5	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 0.5 V, V_{COM} = Open, or V_{NO} = 2.3 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	2.7 V	−2	0.1	2	nA
				Full		−20		20	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 0.5 V, V_{NO} = Open, or V_{COM} = 2.3 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	2.7 V	−2	0.1	2	nA
				Full		−20		20	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		1.8		5.5	V
Input logic low	V_{IL}			Full		0		0.6	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	2.7 V	−2	0.3	2	nA
				Full		−20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 2.5-V Supply(1) (continued)

V_+ = 2.3 V to 2.7 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	2.5 V	3	7	10	ns
				Full	2.3 V to 2.7 V	2.5		10.5	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	2.5 V	6.5	9.5	13	ns
				Full	2.3 V to 2.7 V	5		15	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 20	25°C	2.5 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		19		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		18		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	2.5 V		36.5		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	2.5 V		36.5		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	2.5 V		2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	2.5 V		200		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 19	25°C	2.5 V		−64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	2.5 V		0.02		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	2.7 V		0.01	0.1	µA
				Full				0.15	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 1.8-V Supply(1)

V_+ = 1.65 V to 1.95 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
Peak ON resistance	r_{peak}	$0 \le V_{NO} \le V_+$, I_{COM} = −2 mA,	Switch ON, See Figure 13	25 °C	1.65 V		3.7	25	Ω
				Full				30	
ON-state resistance	r_{on}	V_{NO} = 1.5 V, I_{COM} = −2 mA,	Switch ON, See Figure 13	25°C	1.65 V		1.5	3.4	Ω
				Full				3.5	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = −2 mA	Switch ON, See Figure 13	25°C	1.65 V		1.5		Ω
		V_{NO} = 0.6 V, 1.5 V, I_{COM} = −2 mA	Switch ON, See Figure 13	25°C			2	6	
				Full				6	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 0.3 V, V_{COM} = 1.65 V, or V_{NO} = 1.65 V, V_{COM} = 0.3 V	Switch OFF, See Figure 14	25°C	1.95 V	−2	0.5	2	nA
				Full		−20		20	
	$I_{NO(PWROFF)}$	V_{NO} = 0 to 1.95 V, V_{COM} = 1.95 V to 0		25°C	0 V	−1	0.1	1	µA
				Full		−5		5	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 0.3 V, V_{NO} = 1.65 V, or V_{COM} = 0.3 V, V_{NO} = 1.65 V	Switch OFF, See Figure 14	25°C	1.95 V	−2	0.5	2	nA
				Full		−20		20	
	$I_{COM(PWROFF)}$	V_{COM} = 0 to 1.95 V, V_{NO} = 1.95 V to 0		25°C	0 V	−1	0.1	1	µA
				Full		−5		5	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 0.3 V, V_{COM} = Open, or V_{NO} = 1.65 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	1.95 V	−2	0.1	2	nA
				Full		−20		20	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 0.3 V, V_{NO} = Open, or V_{COM} = 1.65 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	1.95 V	−2	0.1	2	nA
				Full		−20		20	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		1.5		5.5	V
Input logic low	V_{IL}			Full		0		0.6	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	1.95 V	−2	0.3	2	nA
				Full		−20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 1.8-V Supply(1) (continued)

V_+ = 1.65 V to 1.95 V, T_A = −40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	1.8 V	5.5	9	19	ns
				Full	1.65 V to 1.95 V	5		20	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 17	25°C	1.8 V	7.5	12	17.5	ns
				Full	1.65 V to 1.95 V	6		20	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 20	25°C	1.8 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		19		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		18		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	1.8 V		37		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	1.8 V		37		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	1.8 V		2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	1.8 V		200		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	Switch OFF, See Figure 19	25°C	1.8 V		−64		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	1.8 V		0.05		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	1.95 V		0.01	0.1	µA
				Full				0.1	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

TYPICAL PERFORMANCE

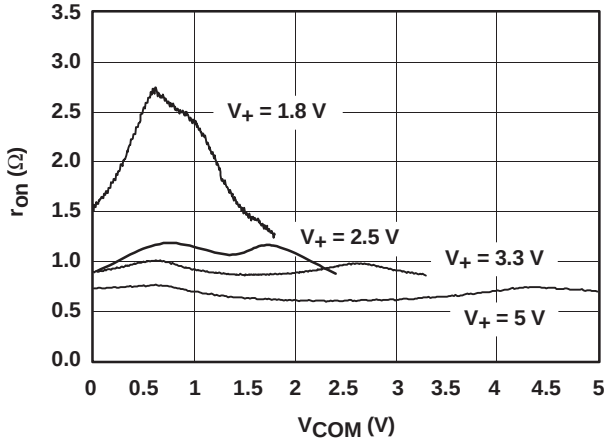


Figure 1. r_{on} vs V_{COM} (T_A = 25°C)

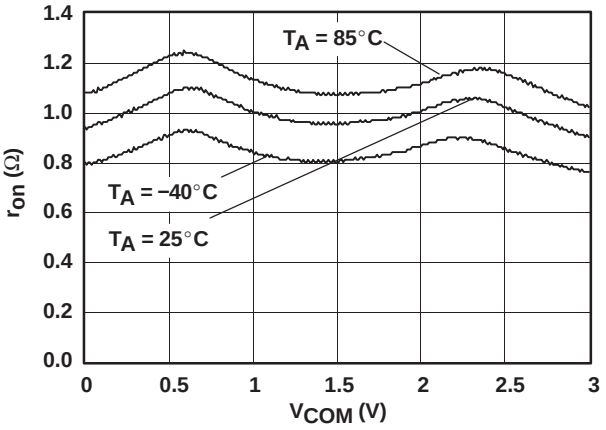


Figure 2. r_{on} vs V_{COM} (V_+ = 3 V)

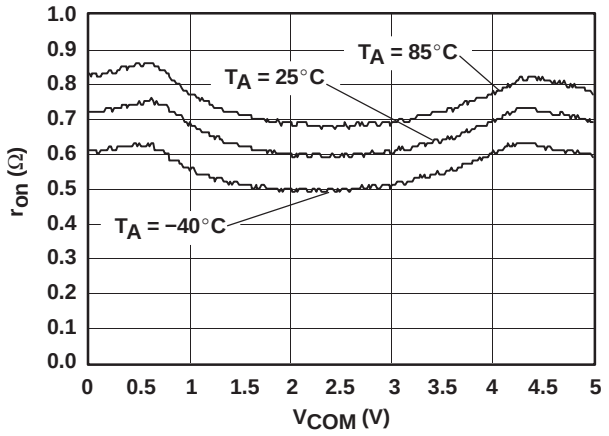


Figure 3. r_{on} vs V_{COM} (V_+ = 5 V)

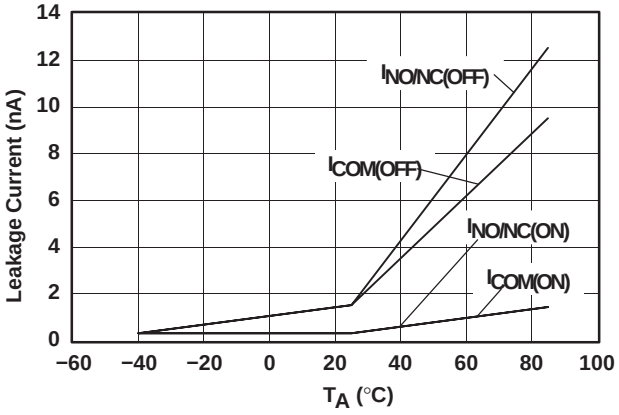


Figure 4. Leakage Current vs Temperature (V_+ = 5.5 V)

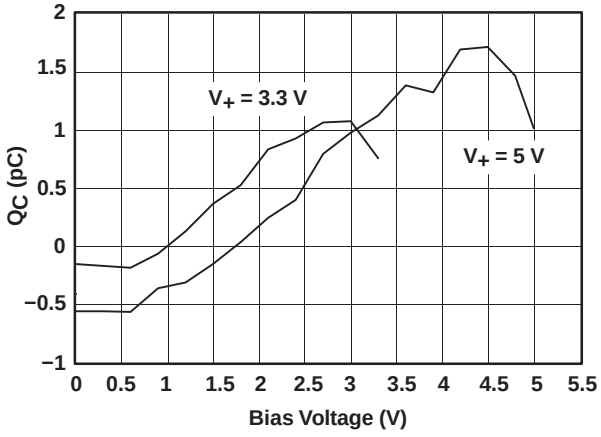


Figure 5. Charge Injection (Q_C) vs Bias Voltage

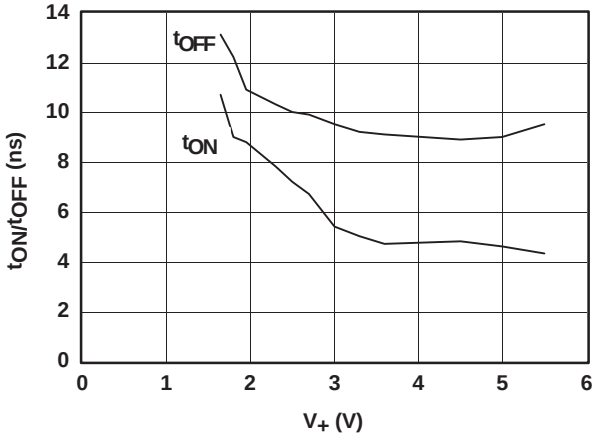


Figure 6. t_{ON} and t_{OFF} vs V_+

TYPICAL PERFORMANCE

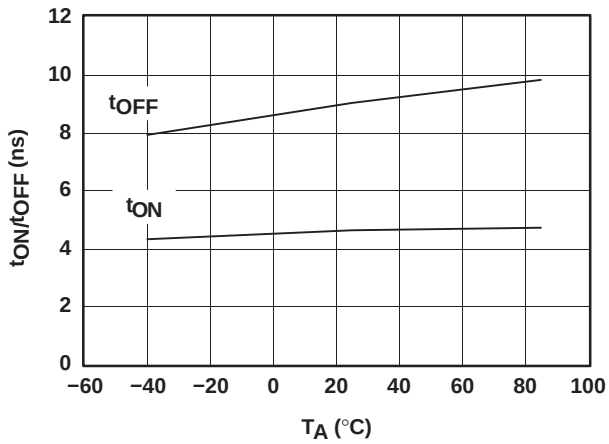


Figure 7. t_{ON} and t_{OFF} vs Temperature (V_+ = 5 V)

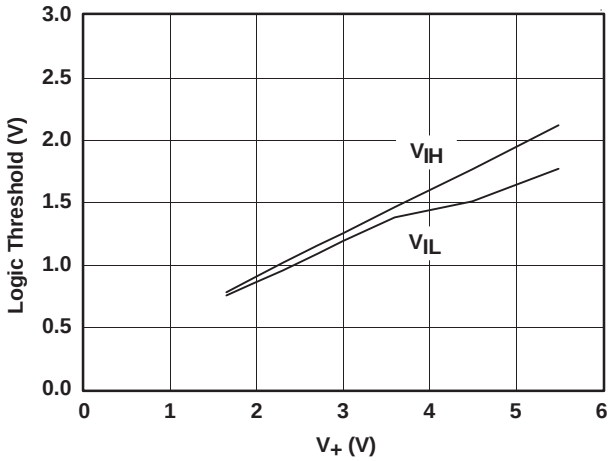


Figure 8. Logic Threshold vs V_+

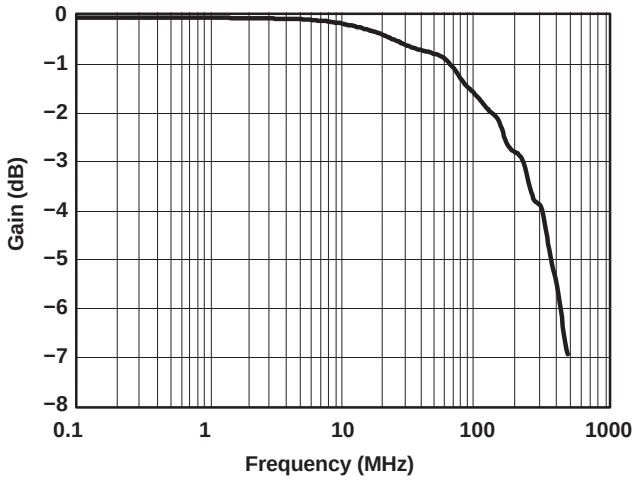


Figure 9. Gain vs Frequency (V_+ = 5 V)

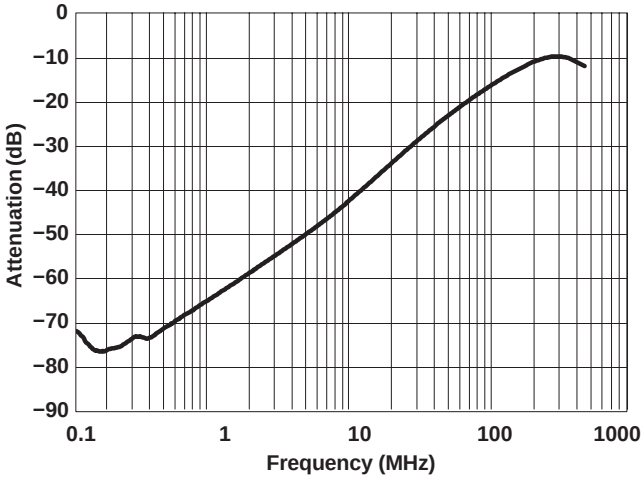


Figure 10. OFF Isolation vs Frequency (V_+ = 5 V)

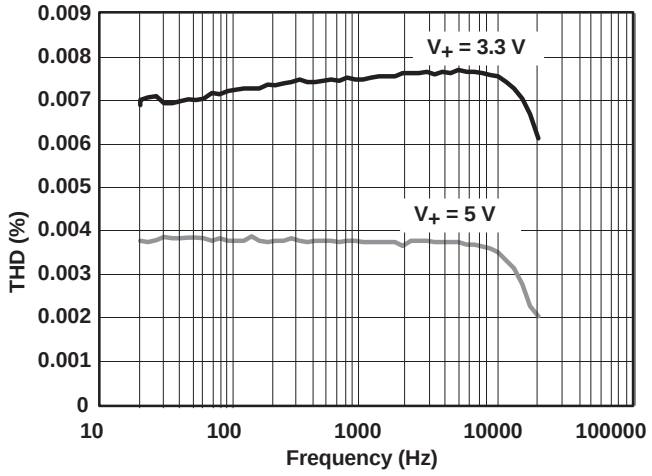


Figure 11. Total Harmonic Distortion vs Frequency (V_+ = 5 V)

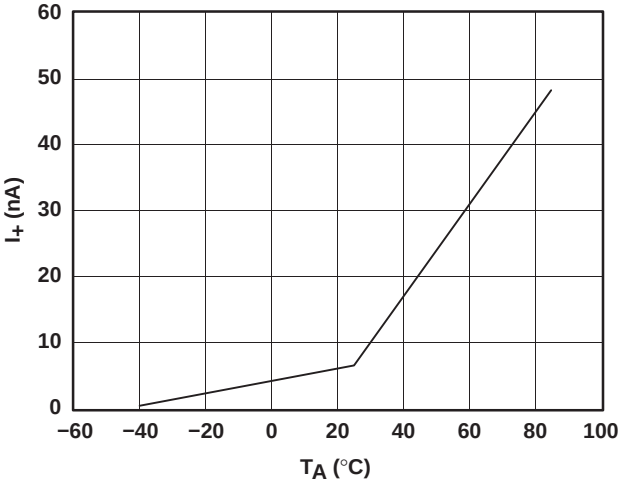


Figure 12. Power-Supply Current vs Temperature (V_+ = 5 V)

PIN DESCRIPTION

PIN NUMBER	NAME	DESCRIPTION
1	NO	Normally open
2	COM	Common
3	GND	Digital ground
4	IN	Digital control pin to connect COM to NO
5	V_+	Power supply

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V_{COM}	Voltage at COM
V_{NO}	Voltage at NO
r_{on}	Resistance between COM and NO ports when the channel is ON
r_{peak}	Peak on-state resistance over a specified voltage range
$r_{on(flat)}$	Difference between the maximum and minimum value of r_{on} in a channel over the specified range of conditions
$I_{NO(OFF)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
$I_{NO(PWROFF)}$	Leakage current measured at the NO port during the power-down condition, $V_+ = 0$
$I_{COM(OFF)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the OFF state under worst-case input and output conditions
$I_{COM(PWROFF)}$	Leakage current measured at the COM port during the power-down condition, $V_+ = 0$
$I_{NO(ON)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
$I_{COM(ON)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the ON state and the output (NO) open
V_{IH}	Minimum input voltage for logic high for the control input (IN)
V_{IL}	Maximum input voltage for logic low for the control input (IN)
V_I	Voltage at the control input (IN)
I_{IH}, I_{IL}	Leakage current measured at the control input (IN)
t_{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning ON.
t_{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning OFF.
Q_C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance, and ΔV_{COM} is the change in analog output voltage.
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
$C_{COM(OFF)}$	Capacitance at the COM port when the corresponding channel (COM to NO) is OFF
$C_{NO(ON)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NO) is ON
C_I	Capacitance of control input (IN)
O_{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NO to COM) in the OFF state.
BW	Bandwidth of the switch. This is the frequency at which the gain of an ON channel is −3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
I_+	Static power-supply current with the control (IN) pin at V_+ or GND

PARAMETER MEASUREMENT INFORMATION

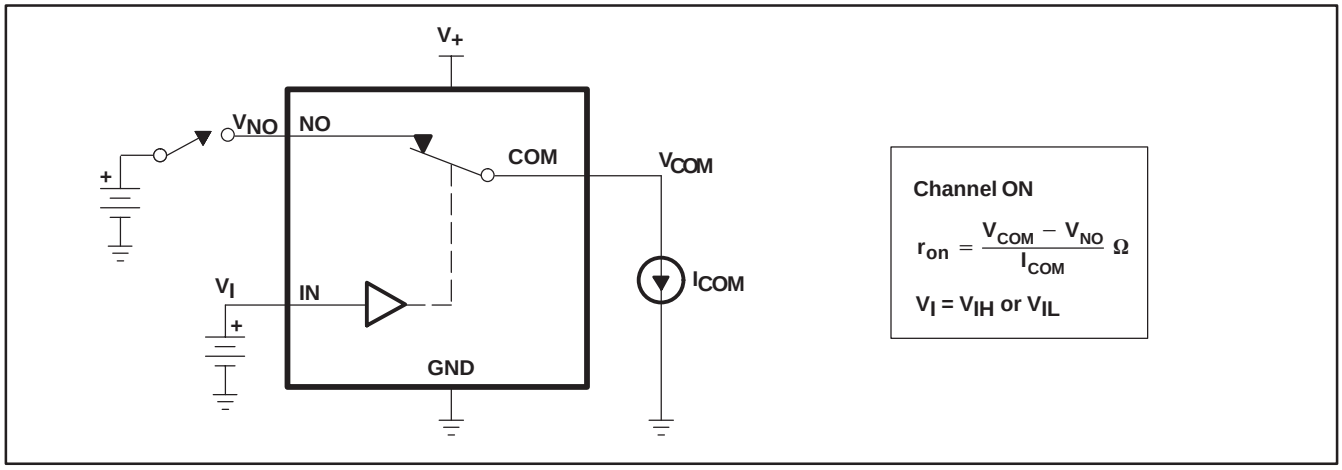


Figure 13. ON-State Resistance (r_{on})

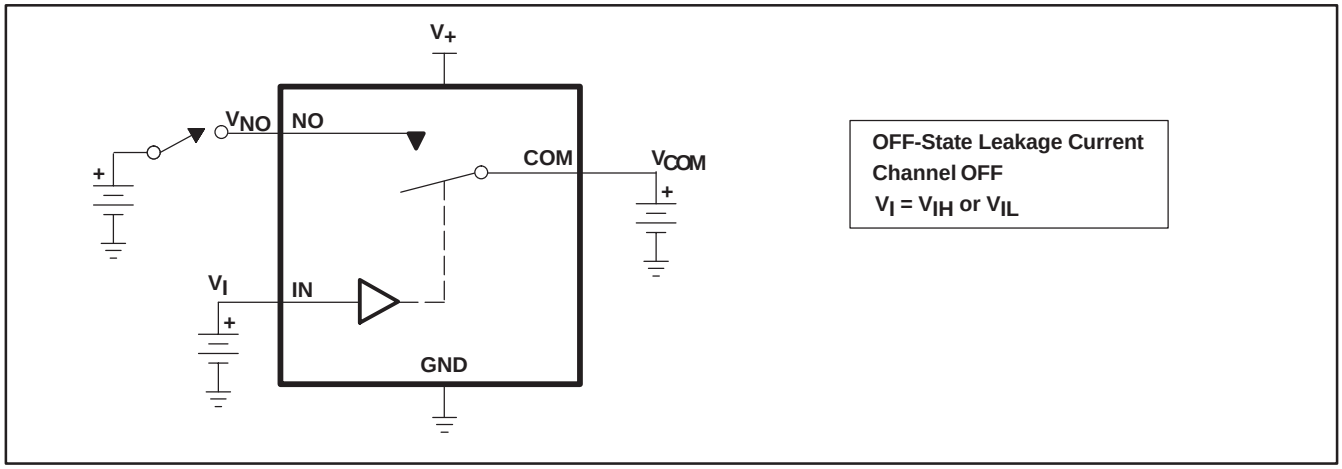


Figure 14. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NO(OFF)}$, $I_{COM(PWROFF)}$, $I_{NO(PWROFF)}$)

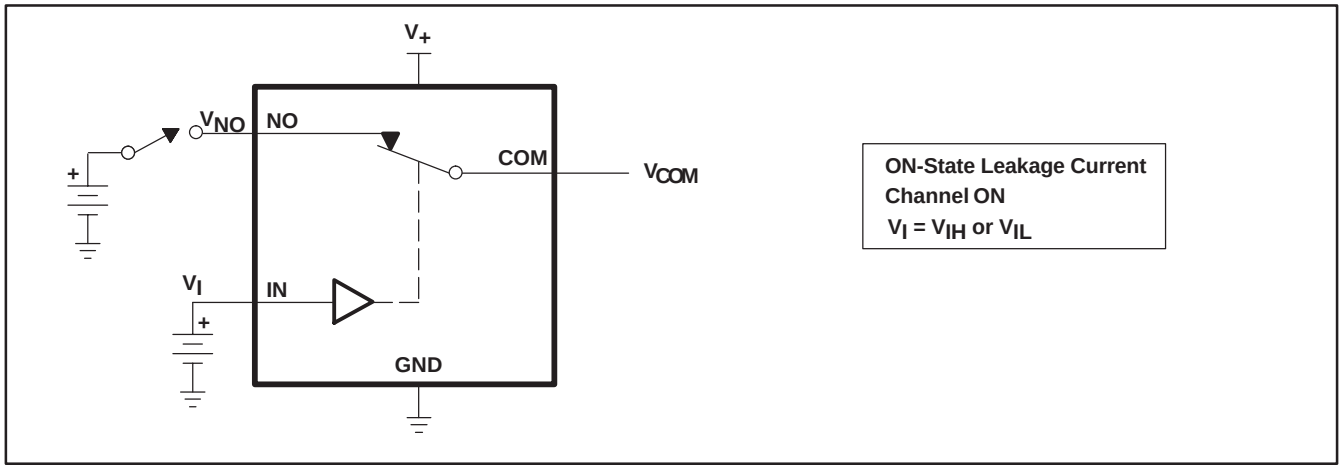


Figure 15. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NO(ON)}$)

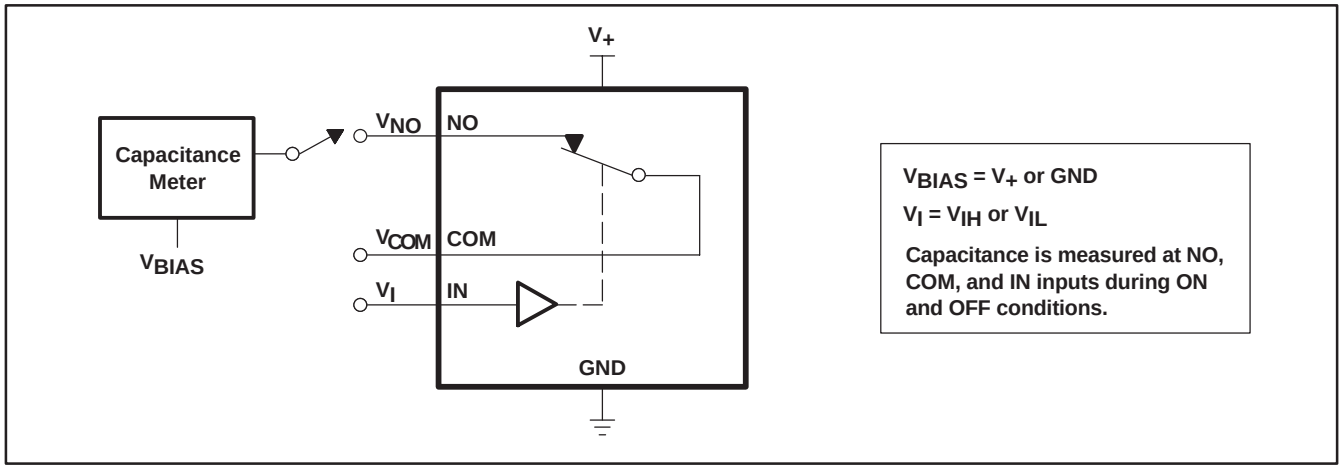
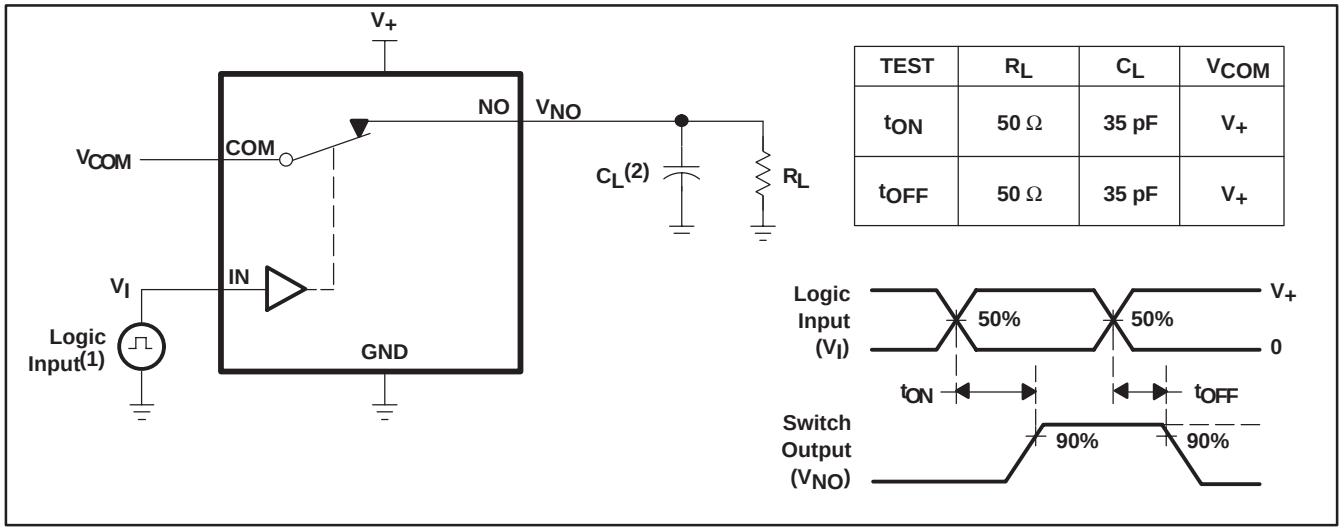


Figure 16. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NO(OFF)}$, $C_{NO(ON)}$)



(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 17. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

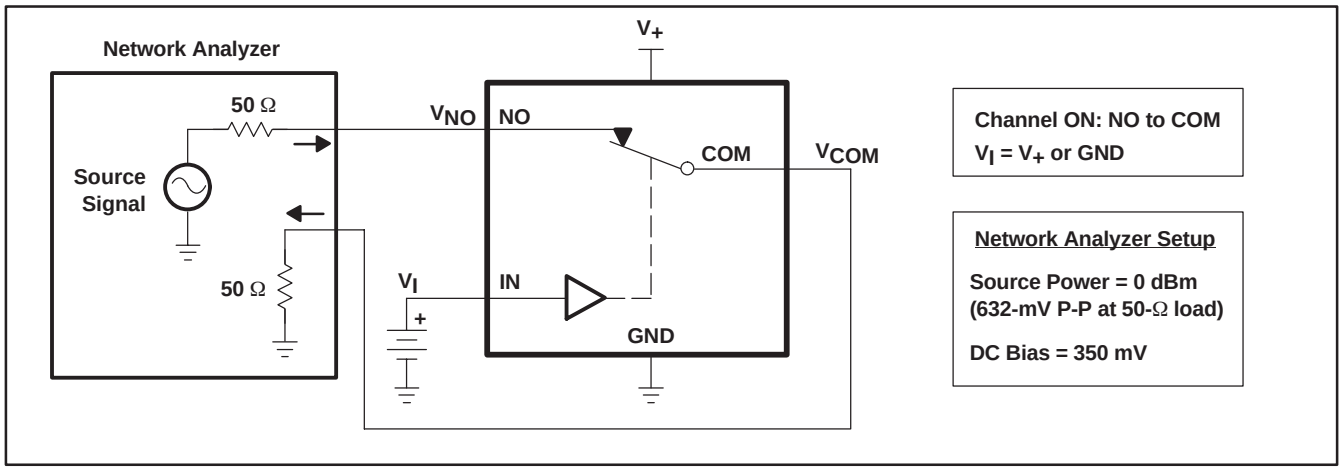


Figure 18. Bandwidth (BW)

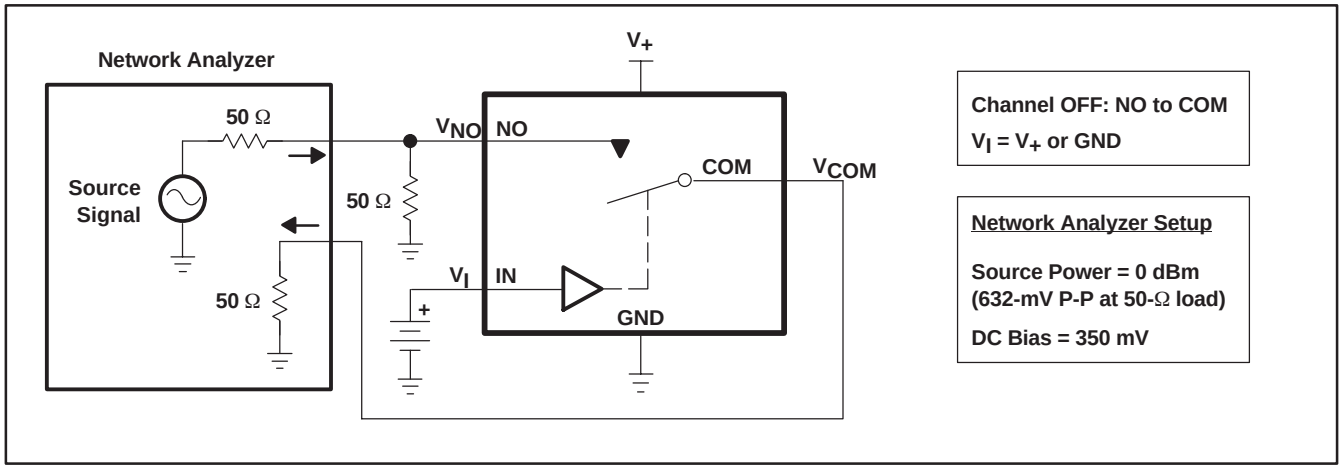
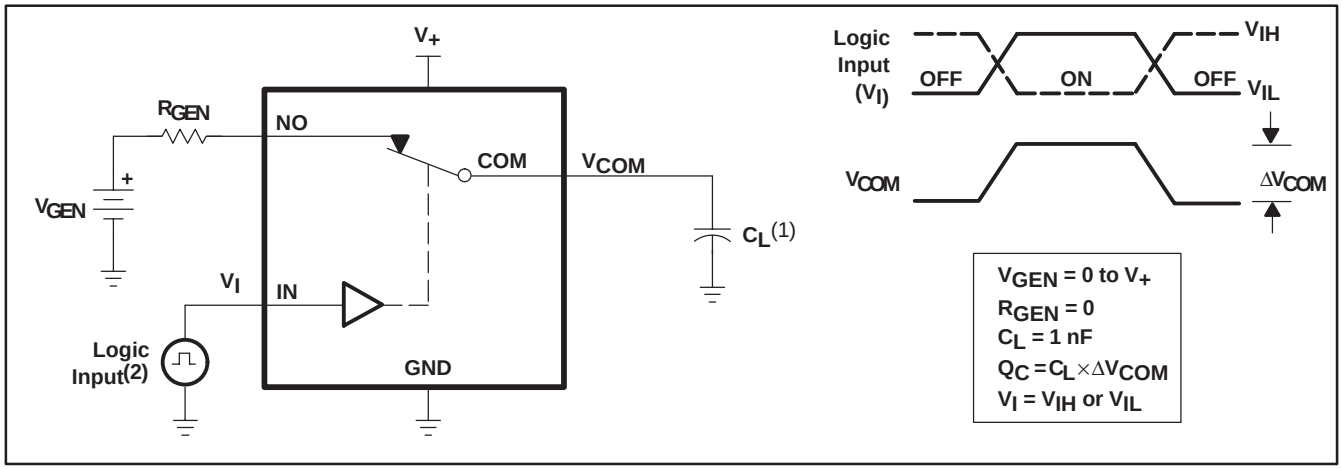
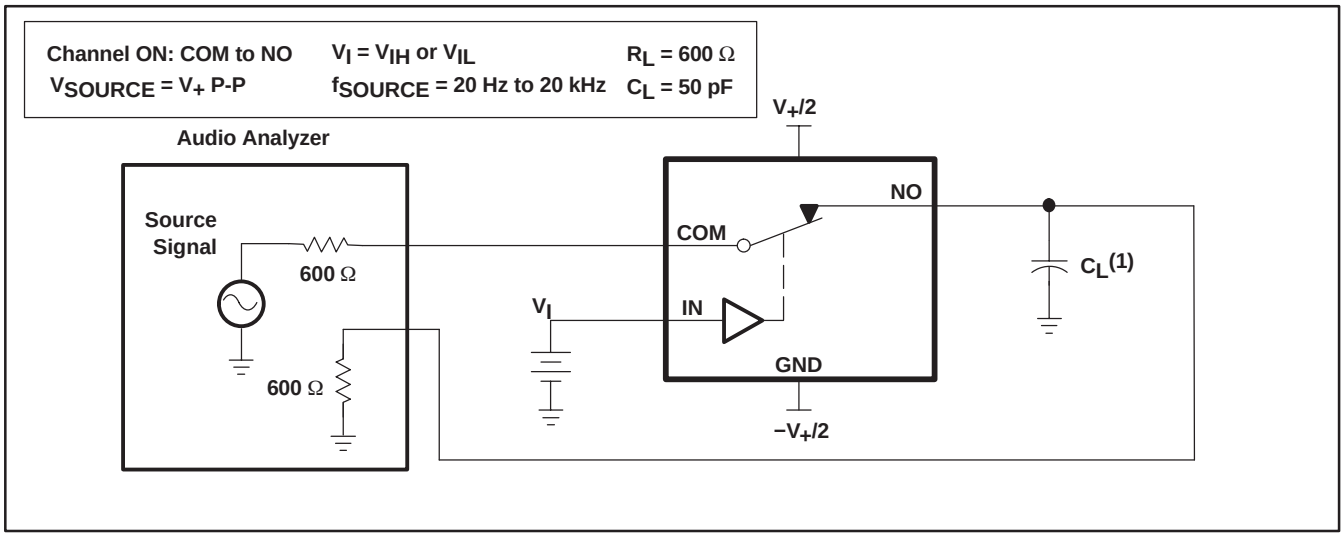


Figure 19. OFF Isolation (O_{ISO})



(1) C_L includes probe and jig capacitance.
(2) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

Figure 20. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 21. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

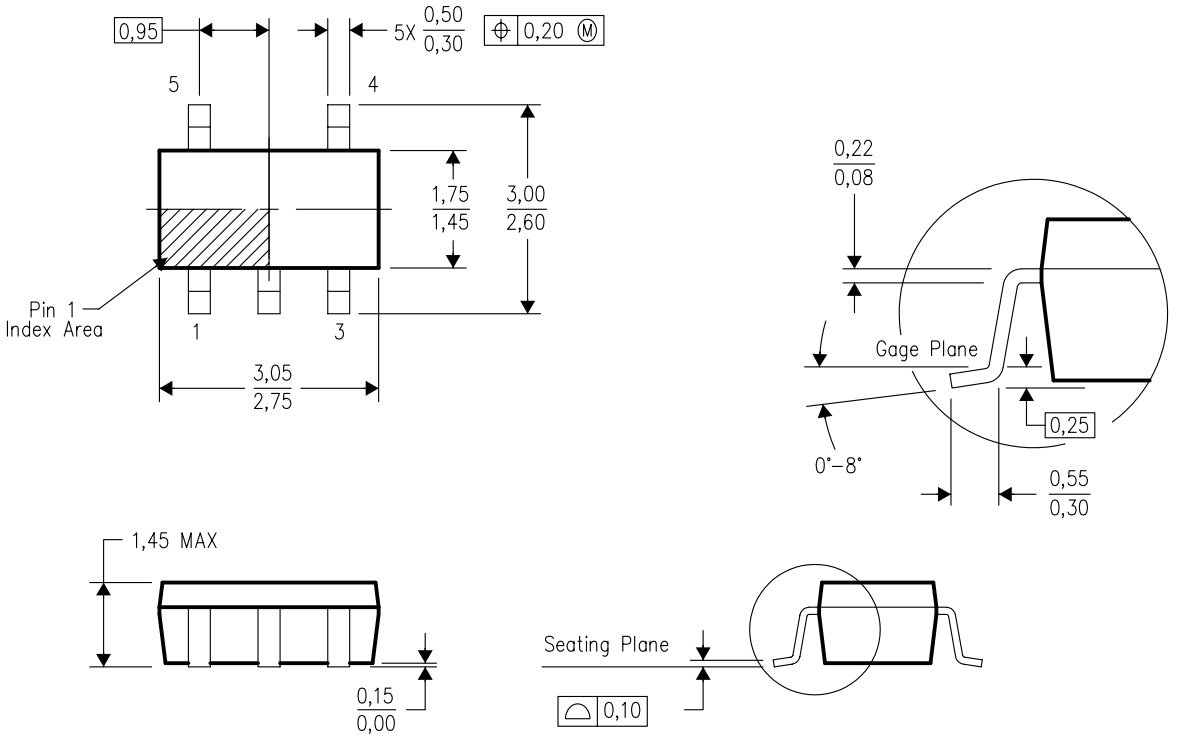
Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
TS5A3166DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3166DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3166DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3166DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3166YZPR	ACTIVE	WCSP	YZP	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

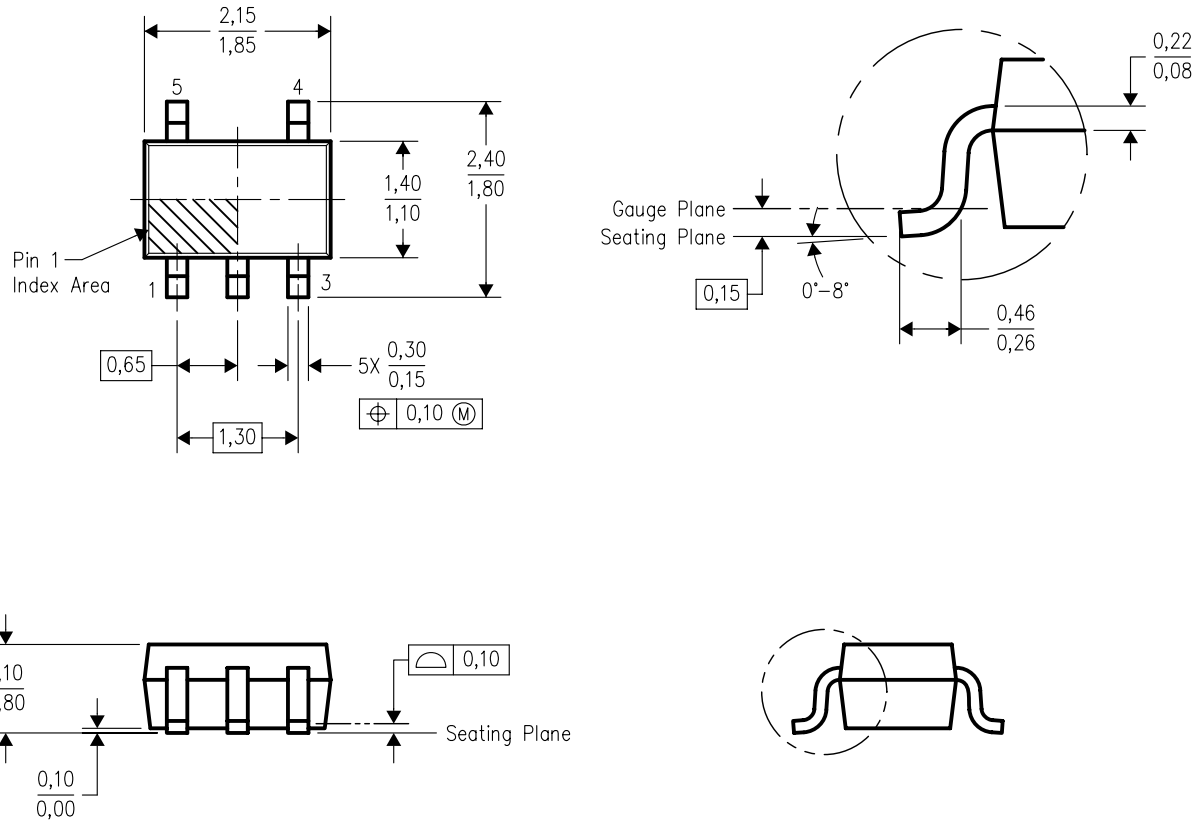
DBV (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4073253–4/K 03/2006

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–178 Variation AA.

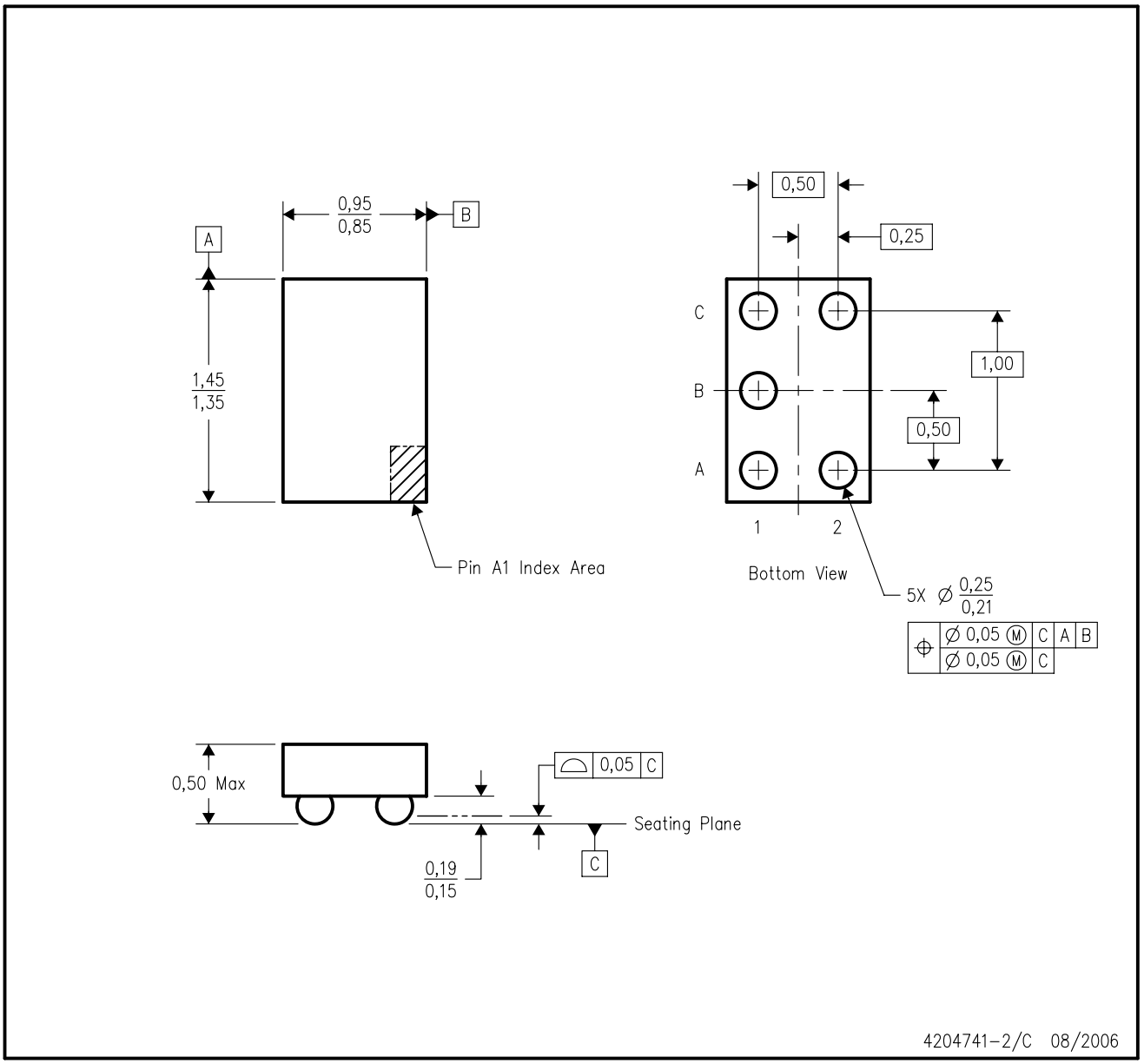
DCK (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4093553–3/F 07/2006

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AA.

YZP (R–XBGA–N5) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.
D. This package is lead–free. Refer to the 5 YEP package (drawing 4204725) for tin–lead (SnPb).

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